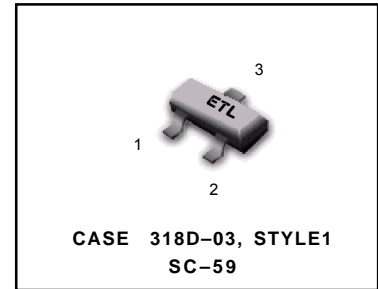
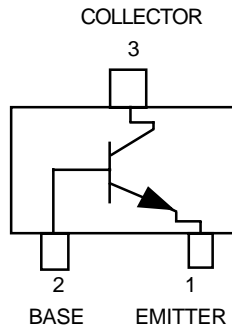


NPN RF Amplifier Transistors

Surface Mount

MSC2295-BT1
MSC2295-CT1



MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	30	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	20	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	5.0	Vdc
Collector Current - Continuous	I _C	30	mAdc

THERMAL CHARACTERISTICS

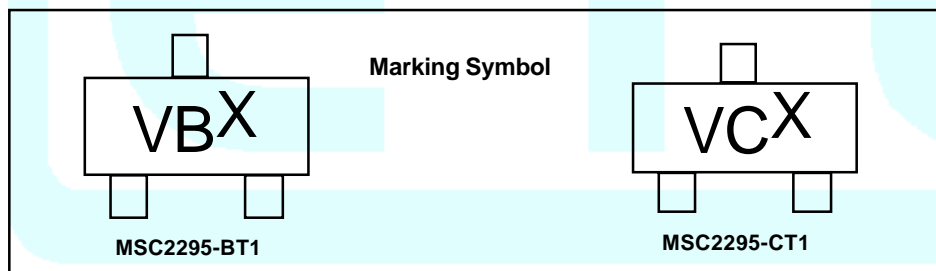
Characteristic	Symbol	Max	Unit
Power Dissipation	P _D	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Max	Unit
Collector-Base Cutoff Current (V _{CB} = 10 Vdc, I _E = 0)	I _{CBO}	—	0.1	μAdc
DC Current Gain ⁽¹⁾ (V _{CB} = 10 Vdc, I _C = -1.0 mAdc)	MSC2295-BT1 MSC2295-CT1	70 110	140 220	—
Collector-Gain - Bandwidth Product (V _{CB} = 10 Vdc, I _E = -1.0 mAdc)	f _T	150	—	MHz
Reverse Transistor Capacitance (V _{CE} = 10 Vdc, I _C = 1.0 mAdc, f = 10.7 MHz)	C _{re}	—	1.5	pF

1. Pulse Test: Pulse Width ≤ 300 ms, D.C. ≤ 2%.

DEVICE MARKING



The "X" represents a smaller alpha digit Date Code. The Date Code indicates the actual month in which the part was manufactured.